

isc Silicon PNP Darlington Power Transistor

# 2SB1492

#### **DESCRIPTION**

- · High DC Current Gain-
- :  $h_{FE}$ = 5000(Min)@ $I_{C}$ = -5A
- · Low-Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= -2.5V(Max.)@I<sub>C</sub>= -5A
- Complement to Type 2SD2254
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

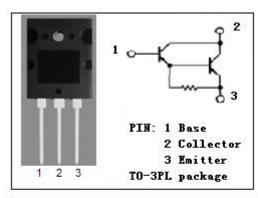
# **APPLICATIONS**

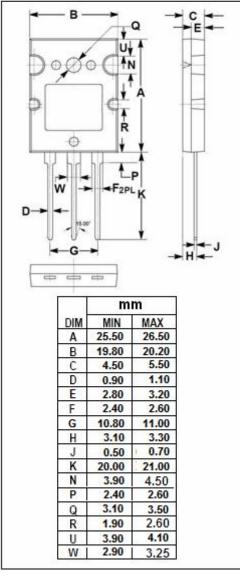


· Designed for power amplifier applications. · Optimum for 60W HiFi output applications.

# ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-130	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-110	V	
V <sub>EBO</sub>	Emitter-Base Voltage	V		
lc	Collector Current-Continuous	Α		
Ісм	Collector Current-Peak	Α		
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25°C	70	w	
	Collector Power Dissipation @ $T_a$ =25 $^{\circ}$ C	3.5		
TJ	Junction Temperature	150 °C		
T <sub>stg</sub>	Storage Temperature Range -55~150		${\mathbb C}$	







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#### **ELECTRICAL CHARACTERISTICS**

## $T_{\text{C}}$ =25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-110			V	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -5mA			-2.5	V	
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -5mA			-3.0	V	
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -130V; I <sub>E</sub> = 0			-100	μА	
Iceo	Collector Cutoff Current	V <sub>CE</sub> = -110V; I <sub>B</sub> = 0			-100	μА	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-100	μА	
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	2000				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -5V	5000		30000		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V		20		MHz	
Switching Times							
t <sub>on</sub>	Turn-on Time			0.9		μ <b>S</b>	
t <sub>stg</sub>	Storage Time	$I_{C}$ = -5A; $I_{B1}$ = - $I_{B2}$ = -5mA, $V_{CC}$ = -50V,		2.5		μ <b>S</b>	
t <sub>f</sub>	Fall Time			1.7		μ \$	

## ♦ h<sub>FE-2</sub> Classifications

Q	Р		
5000-15000	8000-30000		



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